

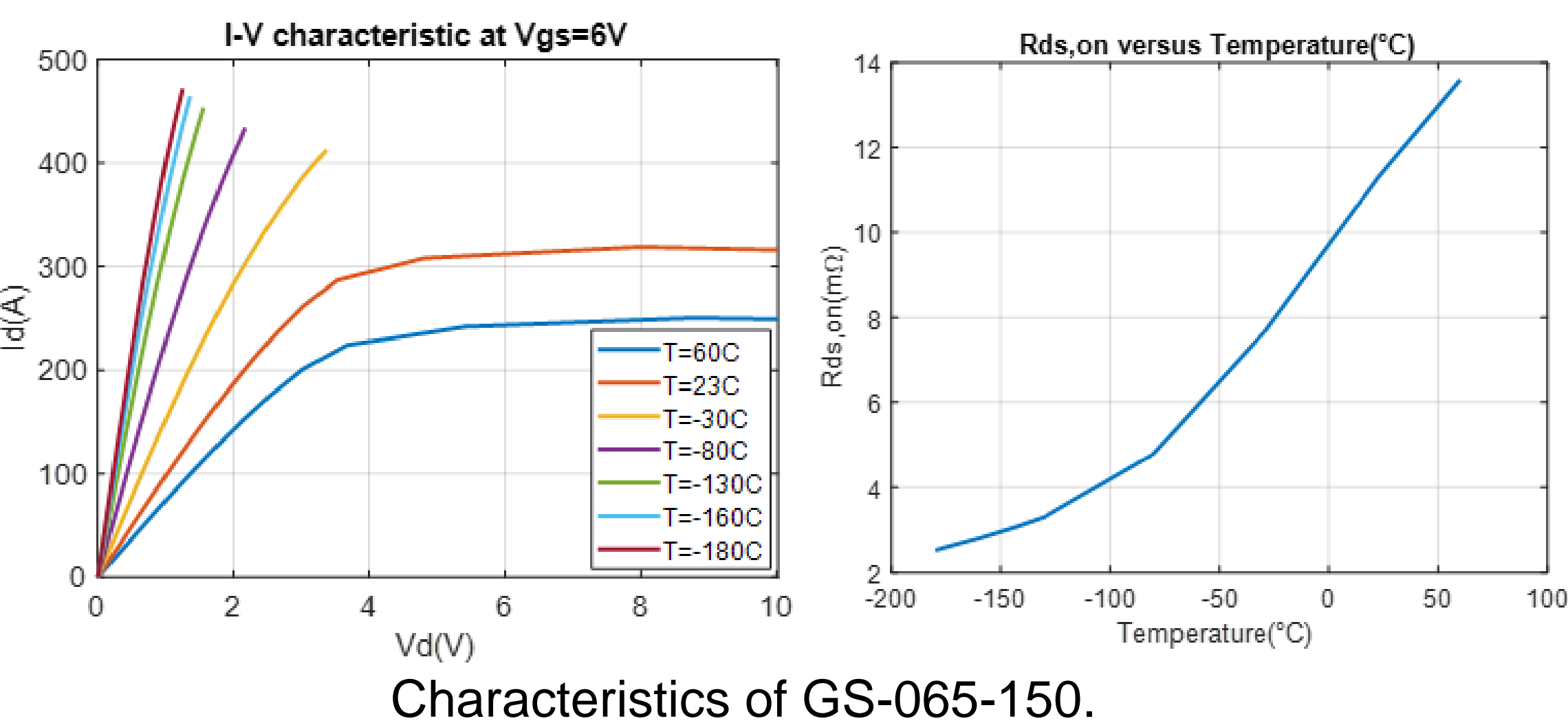
Ching-Hsiang Yang¹, Shimul K. Dam¹, Zhou Dong², Dehao Qin³, Ruirui Chen¹, Fred Wang^{1,4}, Hua Bai¹, Zheyu Zhang³
¹CURENT, University of Tennessee Knoxville, ²ABB. Inc., ³Clemson University, ⁴Oak Ridge National Laboratory

INTRODUCTION

- The cryogenic cooling in the future Electrified Aircraft Propulsion (EAP) system help reduce the loss and increase the power density of the power electronics systems.
- Solid state circuit breaker (SSCB) has advantages of fast current interruption, size and weight reduction, and providing additional functions, but offers lower efficiency.
- A cryogenically cooled GaN-HEMT based SSCB module is proposed, which can achieve higher than 99.9% efficiency and high over-current interruption capability.

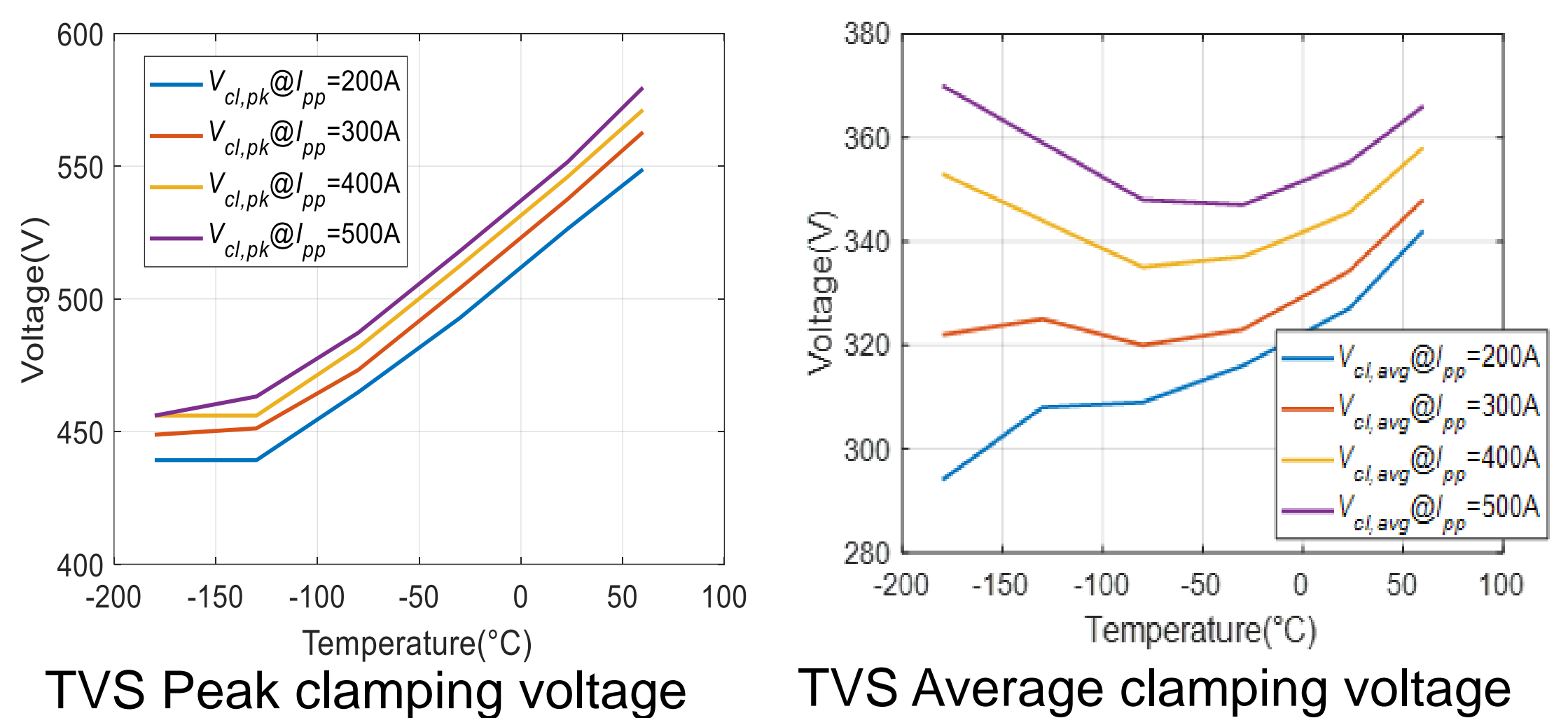
MAIN COMPONENTS SELECTION

- GaN HEMTs at cryogenic temperature:
 - ✓ About 5x on-resistance reduction
 - ✓ Allow higher current without any saturation



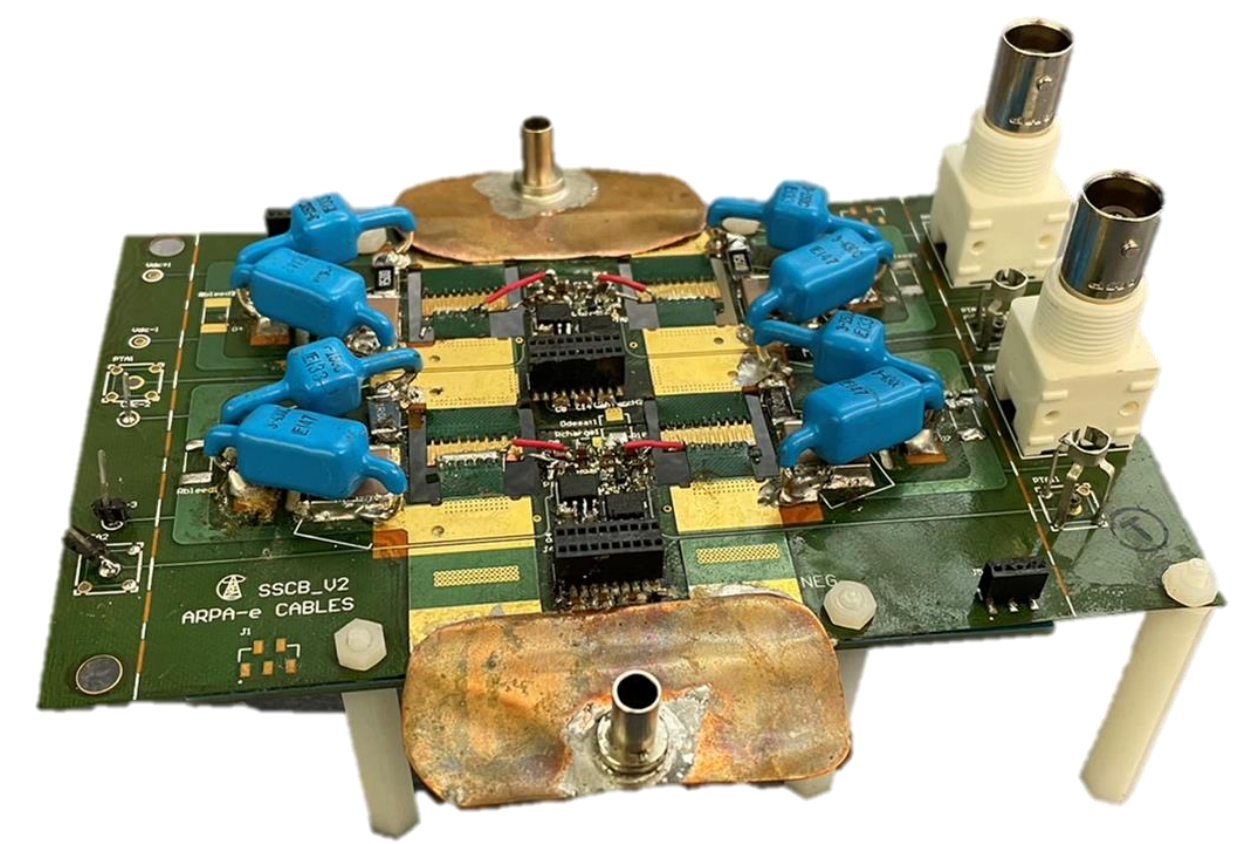
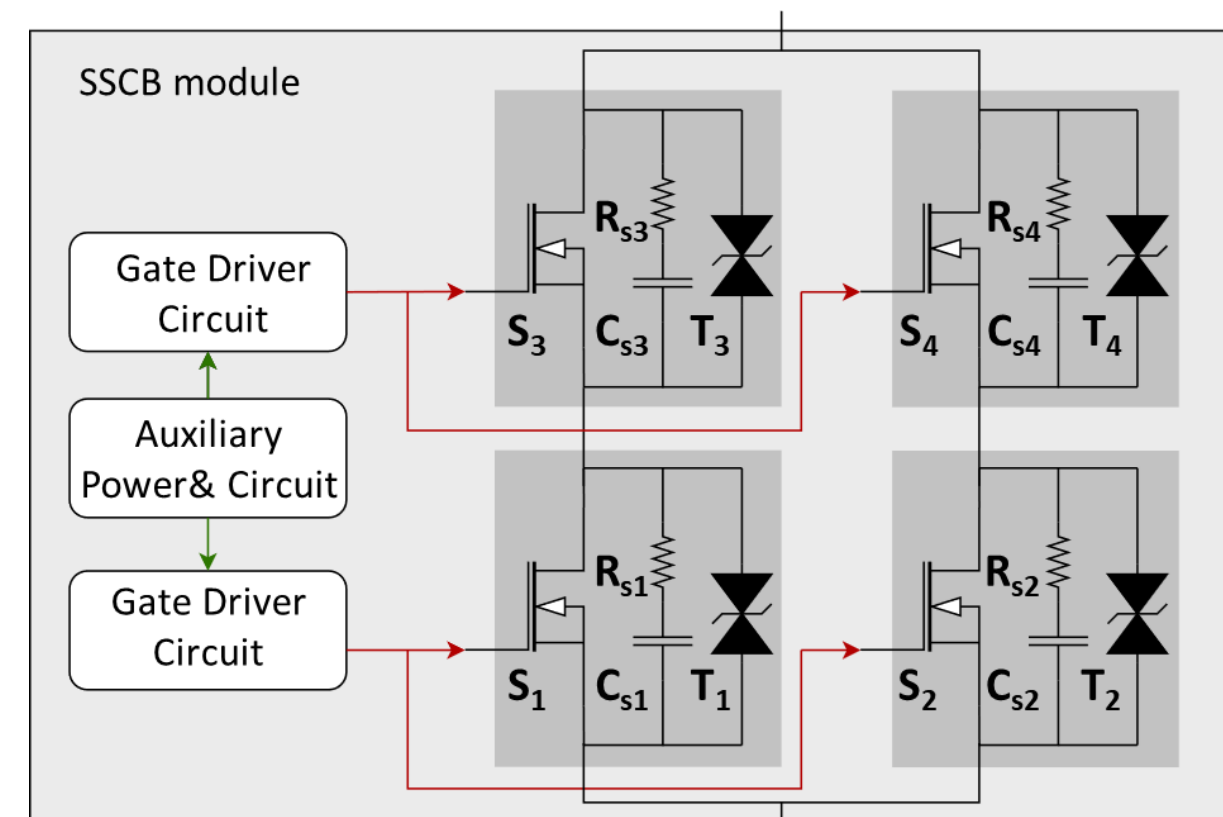
- TVS diode at cryogenic temperature:

- ✓ Lower peak clamping voltage
- ✓ Higher average clamping voltage
- ✓ Reduced clamping ratio



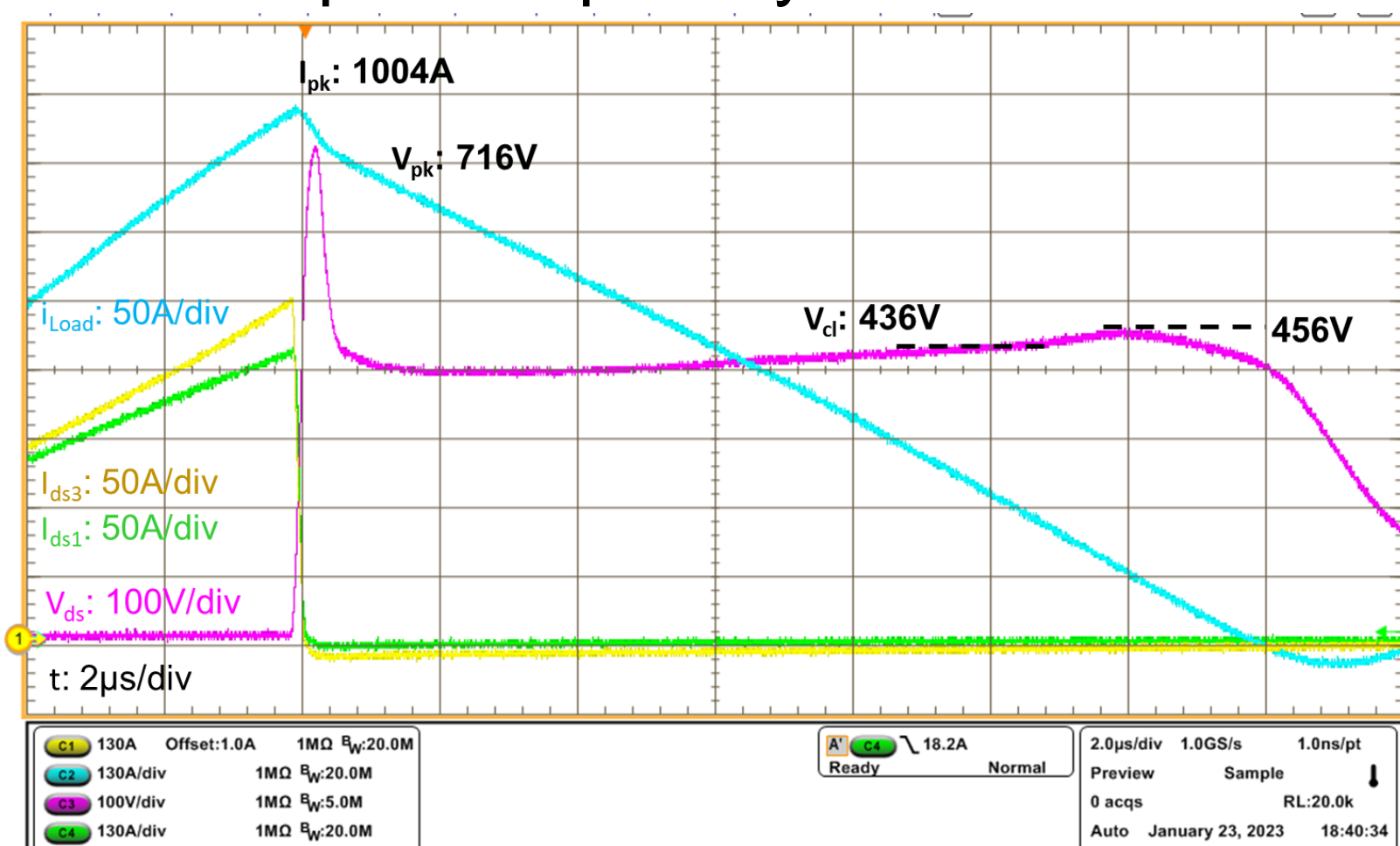
SSCB MODULE DESIGN

- Module ratings: 750V/100A
- Module design key points
 - ✓ Cell design to minimized the gate-loop and power-loop inductance
 - ✓ TVS diodes in “V-shape” eliminates the extra traces on the PCB to prevent additional stray inductance.

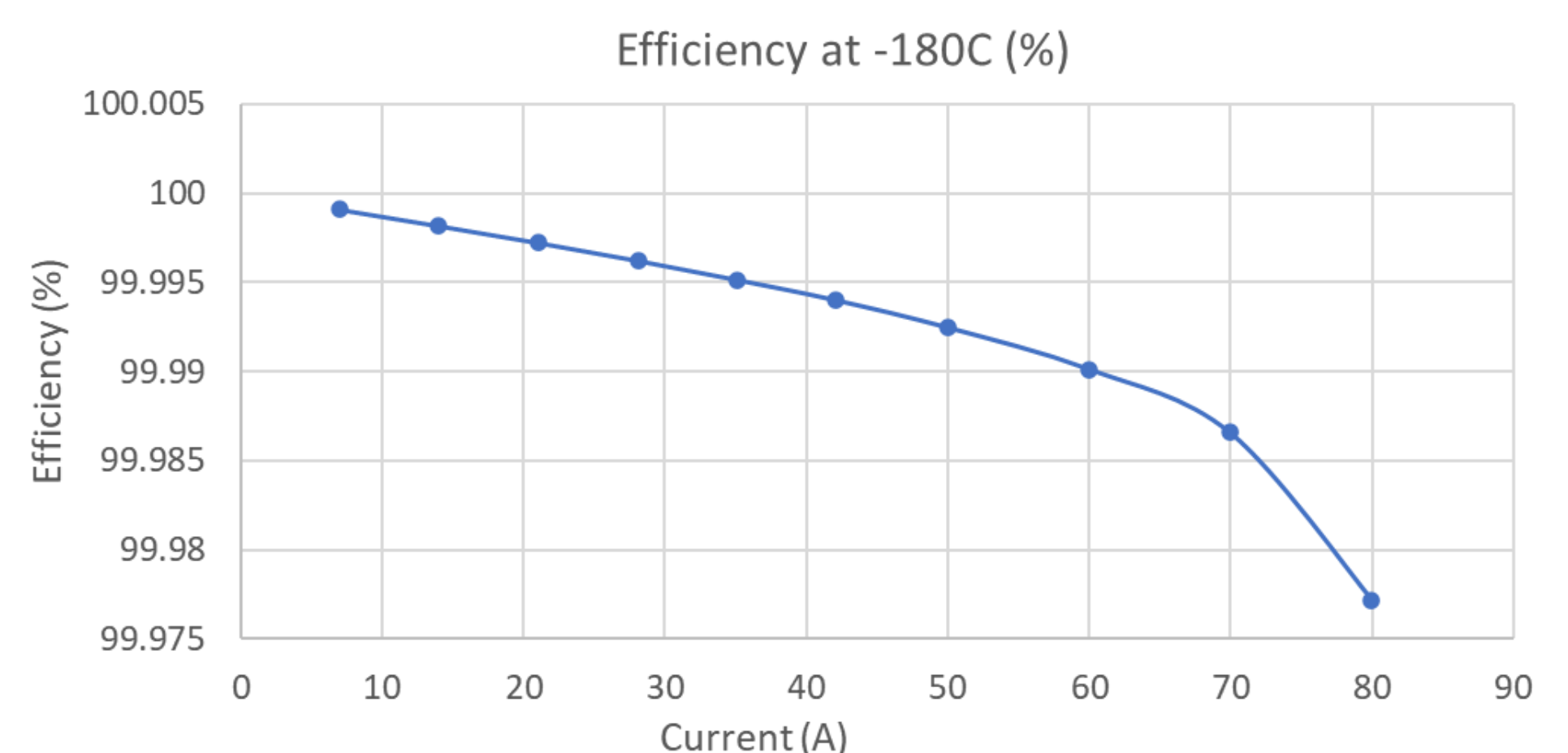


EXPERIMENT RESULTS

- Fault interruption capability



- High efficiency



CONCLUSION

- A GaN-based cryogenically cooled 750 V/ 100 A SSCB module is proposed based on components characteristics at cryogenic temperature and specification requirements.
- Experimental results validated the capability of the proposed SSCB to interrupt up to 10x (1kA) fault current.
- The measured efficiency is >99.9% up to 80 A for the prototype SSCB module.

